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2015年8月

FCPF850N80Z

N 沟道 SuperFET[®] II MOSFET

800 V, 8 A, 850 mΩ

特性

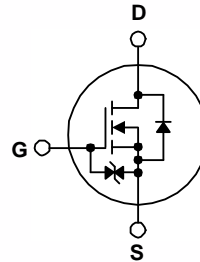
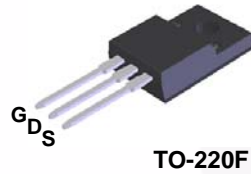
- 典型值 $R_{DS(on)} = 710 \text{ m}\Omega$ (典型值)
- 超低栅极电荷 (典型值 $Q_g = 22 \text{ nC}$)
- 低 E_{oss} (典型值 $2.3 \text{ uJ @ } 400 \text{ V}$)
- 低有效输出电容 (典型值 $C_{oss(eff.)} = 106 \text{ pF}$)
- 100% 经过雪崩测试
- 符合 RoHS 标准
- 改进的 ESD 能力

描述

SuperFET[®] II MOSFET 是飞兆半导体利用电荷平衡技术实现出色的低导通电阻和更低栅极电荷性能的全新高压超级结 (SJ) MOSFET 系列产品。这项技术专用于最小化导通损耗并提供卓越的开关性能、 dv/dt 额定值和更高雪崩能量。此外, 内部栅源极 ESD 二极管允许经受超过 2 kV HBM 冲击压力。因此, SuperFET II MOSFET 非常适合功率开关应用, 如音频、笔记本适配器、照明、ATX 电源和工业电源应用。

应用

- AC-DC 电源
- LED 照明

绝对最大额定值 $T_C = 25^\circ\text{C}$ 除非另有说明。

符号	参数	FCPF850N80Z	单位
V_{DSS}	漏极-源极电压	800	V
V_{GSS}	栅极-源极电压	- DC	± 20
		- AC ($f > 1 \text{ Hz}$)	± 30
I_D	漏极电流	- 连续 ($T_C = 25^\circ\text{C}$)	8.0^*
		- 连续 ($T_C = 100^\circ\text{C}$)	5.1^*
I_{DM}	漏极电流	- 脉冲 (注1)	18^*
E_{AS}	单脉冲雪崩能量 (注2)	114	mJ
I_{AR}	雪崩电流 (注1)	1.2	A
E_{AR}	重复雪崩能量 (注1)	0.284	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	二极管恢复 dv/dt 峰值 (注3)	20	
P_D	功耗	($T_C = 25^\circ\text{C}$)	28.4
		- 高于 25°C 的功耗系数	0.24
T_J, T_{STG}	工作和存储温度范围	-55 至 +150	$^\circ\text{C}$
T_L	用于焊接的最大引脚温度, 距离外壳 1/8", 持续 5 秒	300	$^\circ\text{C}$

* 漏极电流由最高结温的限制, 与散热片

热性能

符号	参数	FCPF850N80Z	单位
$R_{\theta JC}$	结至外壳热阻最大值	4.4	$^\circ\text{C/W}$
$R_{\theta JA}$	结至环境热阻最大值	62.5	

封装标识与订购信息

器件编号	顶标	封装	包装方法	卷尺寸	带宽	数量
FCPF850N80Z	FCPF850N80Z	TO-220F	塑料管	N/A	N/A	50 个

电气特性 $T_C = 25^\circ\text{C}$ 除非另有说明。

符号	参数	测试条件	最小值	典型值	最大值	单位
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关断特性

BV_{DSS}	漏极-源极击穿电压	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	800	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	击穿电压温度系数	$I_D = 1\text{ mA}$, 参考 25°C 数值	-	0.8	-	$\text{V}/^\circ\text{C}$
I_{DSS}	零栅极电压漏极电流	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_C = 125^\circ\text{C}$	-	-	250	
I_{GSS}	栅极-体漏电流	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	± 10	μA

导通特性

$V_{GS(th)}$	栅极阈值电压	$V_{GS} = V_{DS}, I_D = 0.6\text{ mA}$	2.5	-	4.5	V
$R_{DS(on)}$	漏极至源极静态导通电阻	$V_{GS} = 10\text{ V}, I_D = 3\text{ A}$	-	710	850	$\text{m}\Omega$
g_{FS}	正向跨导	$V_{DS} = 20\text{ V}, I_D = 3\text{ A}$	-	3.5	-	S

动态特性

C_{iss}	输入电容	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	990	1315	pF
C_{oss}	输出电容		-	28	37	pF
C_{rss}	反向传输电容		-	0.74	-	pF
C_{oss}	输出电容	$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	15	-	pF
$C_{oss(eff.)}$	有效输出电容	$V_{DS} = 0\text{ V}$ 至 $480\text{ V}, V_{GS} = 0\text{ V}$	-	106	-	pF
$Q_{g(tot)}$	10 V 的栅极电荷总量	$V_{DS} = 640\text{ V}, I_D = 6\text{ A}, V_{GS} = 10\text{ V}$	-	22	29	nC
Q_{gs}	栅极-源极栅极电荷		-	5	-	nC
Q_{gd}	栅极-漏极“米勒”电荷 (注 4)		-	8.6	-	nC
ESR	等效串联电阻	$f = 1\text{ MHz}$	-	2.4	-	Ω

开关特性

$t_{d(on)}$	导通延迟时间	$V_{DD} = 400\text{ V}, I_D = 6\text{ A}, V_{GS} = 10\text{ V}, R_g = 4.7\ \Omega$	-	16	42	ns
t_r	导通上升时间		-	10	30	ns
$t_{d(off)}$	关断延迟时间		-	40	90	ns
t_f	关断下降时间 (注 4)		-	4.5	19	ns

漏极-源极二极管特性

I_S	漏极-源极二极管最大正向连续电流	-	-	8	A	
I_{SM}	漏极-源极二极管最大正向脉冲电流	-	-	18	A	
V_{SD}	漏极-源极二极管正向电压	$V_{GS} = 0\text{ V}, I_{SD} = 6\text{ A}$	-	-	1.2	V
t_{rr}	反向恢复时间	$V_{GS} = 0\text{ V}, I_{SD} = 6\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	318	-	ns
Q_{rr}	反向恢复电荷		-	4.5	-	μC

注:

- 重复额定值: 脉冲宽度受限于最大结温。
- $I_{AS} = 1.2\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, 开始于 $T_J = 25^\circ\text{C}$
- $I_{SD} \leq 8\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, 开始于 $T_J = 25^\circ\text{C}$
- 典型特性本质上独立于工作温度。

典型性能特征

图 1. 导通区域特性

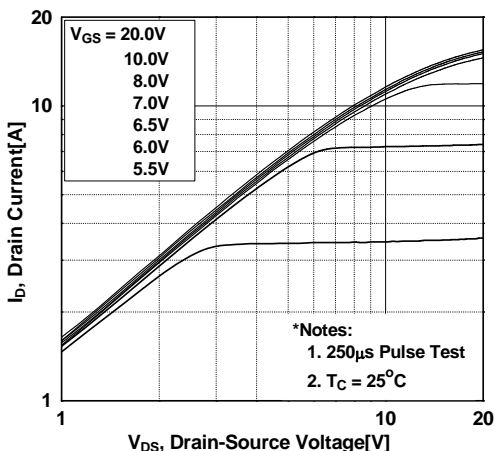


图 2. 传输特性

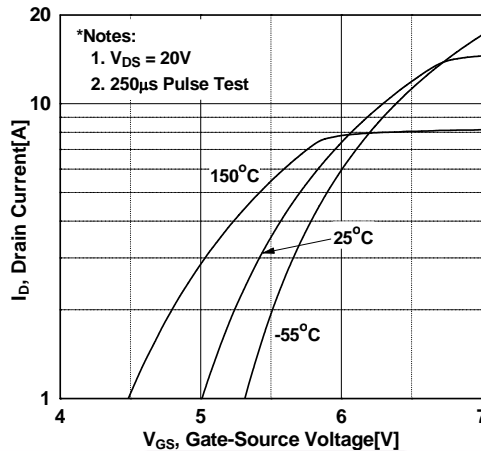


图 3. 导通电阻变化与漏极电流和栅极电压的关系

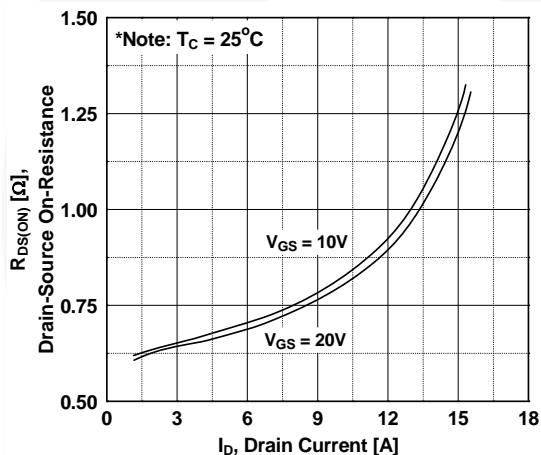


图 4. 体二极管正向电压变化与源极电流和温度的关系

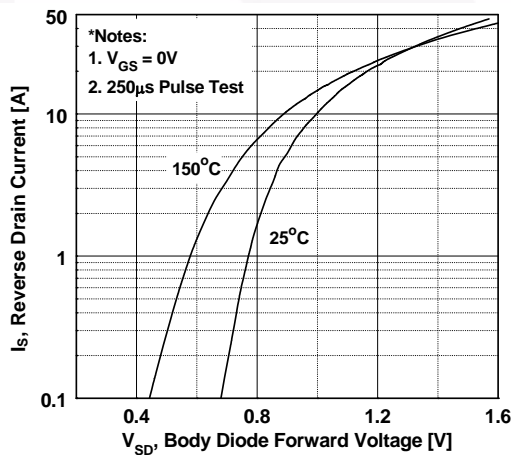


图 5. 电容特性

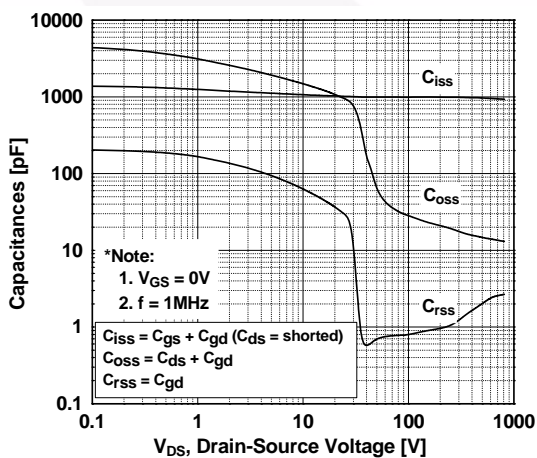
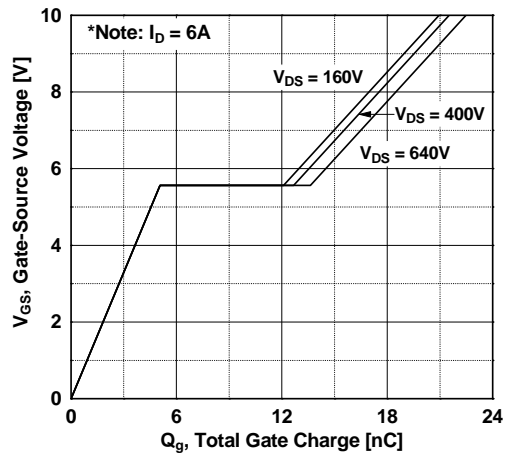


图 6. 栅极电荷特性



典型性能特性 (接上页)

图 7. 击穿电压变化与温度的关系

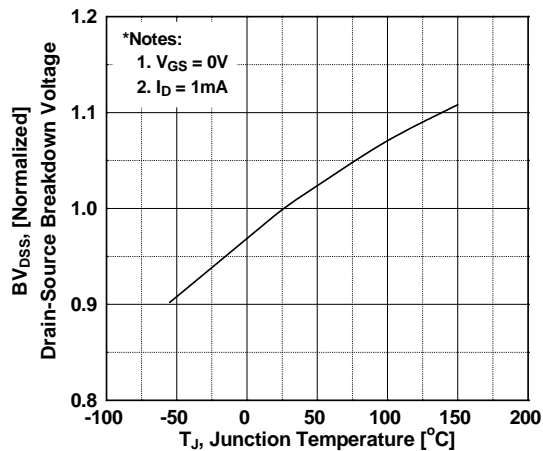


图 8. 导通电阻变化与温度的关系

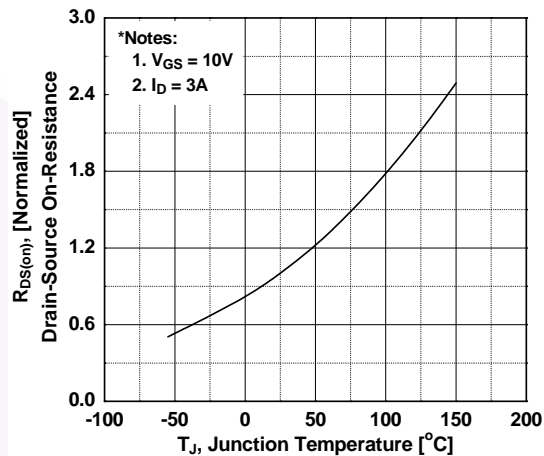


图 9. 最大安全工作区

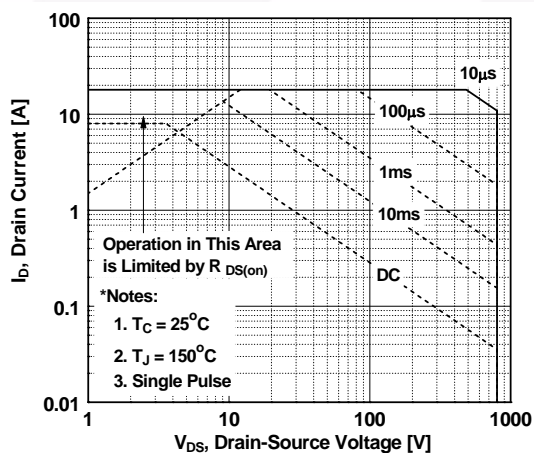


图 10. 最大漏极电流与壳温的关系

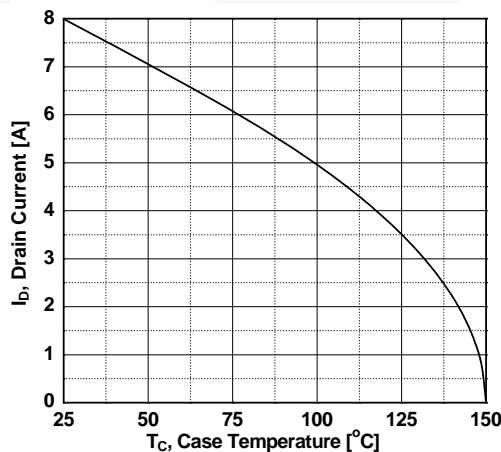
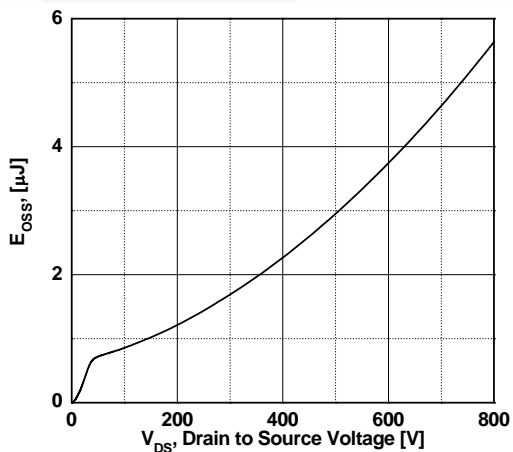
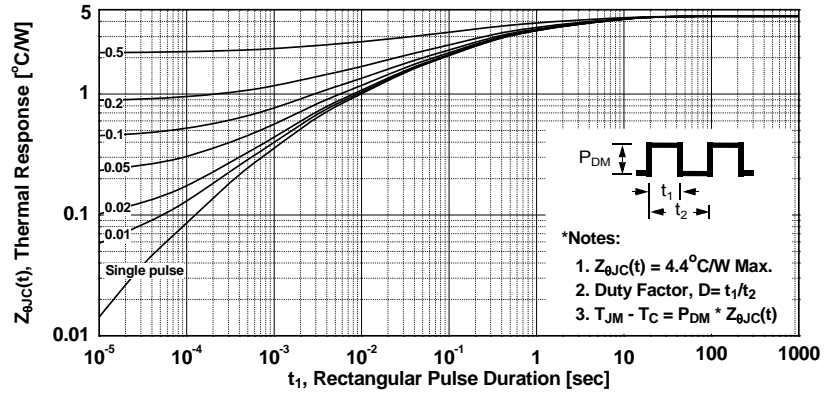


图 11. E_{oss} 和漏极 - 源极电压的关系



典型性能特性 (接上页)

图 12. 瞬态热响应曲线



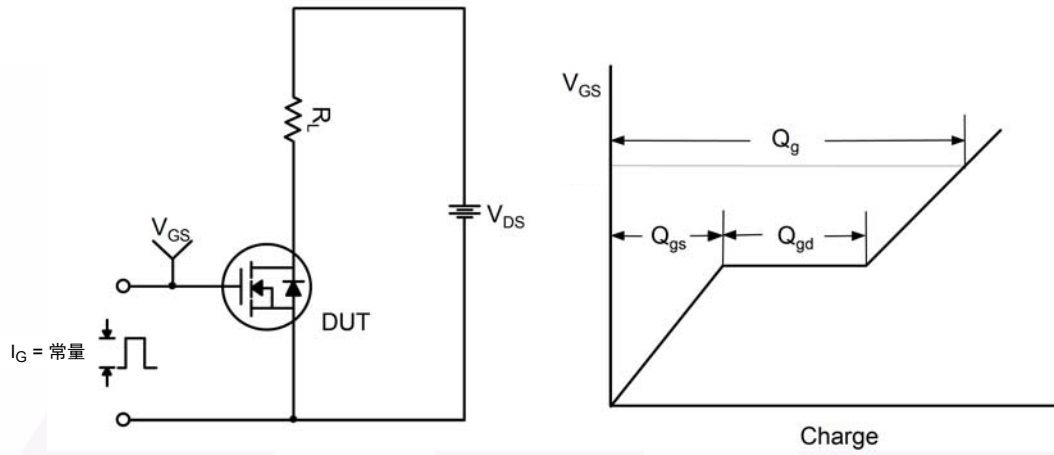


图 13. 栅极电荷测试电路与波形



图 14. 阻性开关测试电路与波形

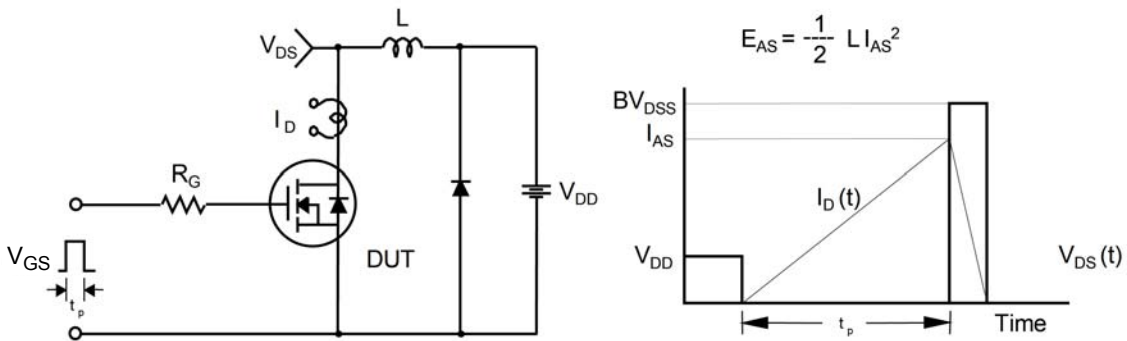


图 15. 非箝位电感开关测试电路与波形

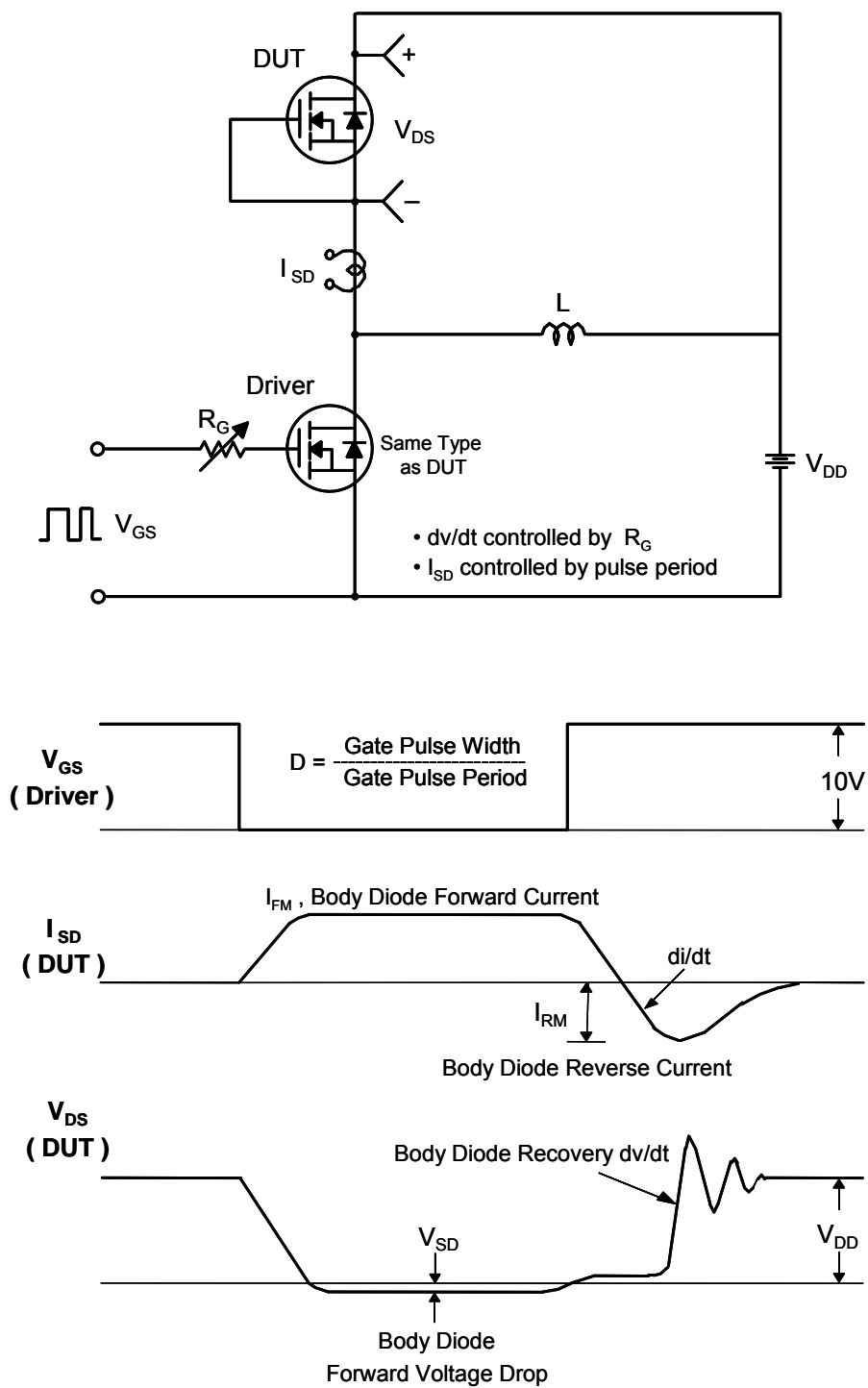
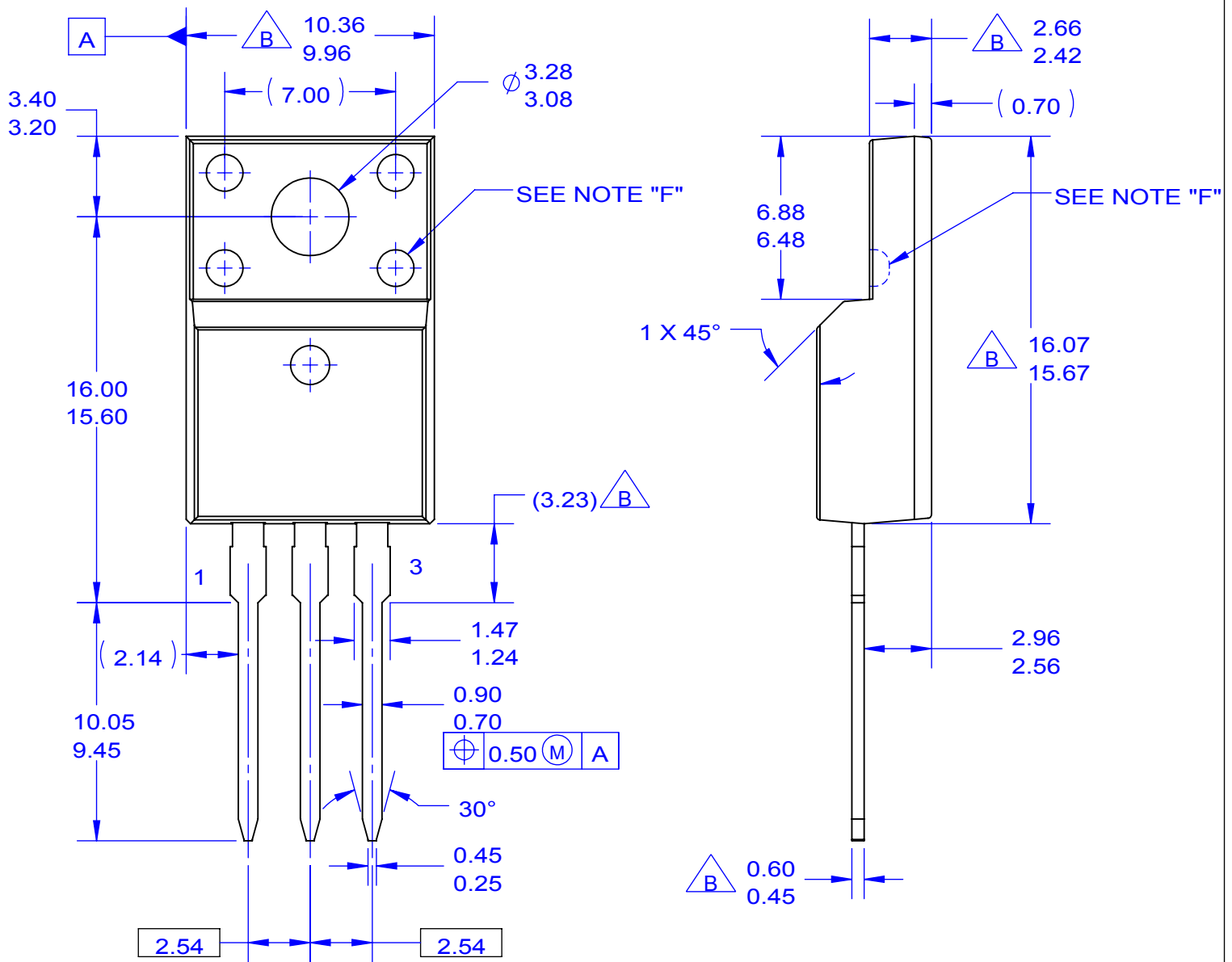


图 16. 二极管恢复 dv/dt 峰值测试电路与波形



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